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1. (Currently Amended) A light emitting device comprising:

a substrate;

a source wiring over said substrate;

a gate wiring over said substrate;

at least one thin film transistor provided in an intersection of said source wiring and said gate wiring;

an insulator over said thin film transistor;

an anode first electrode formed on said insulator;

a cathode second electrode formed on said insulator second to be in contact with said anode first electrode; and

a light emitting layer formed between said anode and eathode first and second electrodes on said insulator

wherein said thin film transistor is electrically connected to said first electrode.

2. (Currently Amended) A light emitting device comprising:

a substrate;

a source wiring over said substrate;

a gate wiring over said substrate;

at least one thin film transistor provided in an intersection of said source wiring and said gate wiring;

an insulator over said thin film transistor;

an anode a first electrode formed on said insulator;

a cathode a second electrode formed on said insulator so as not to be in contact with said anode first electrode; and

a light emitting layer formed between said anode and said eathode first and second electrodes on said insulator,

wherein said anode and said cathode first and second electrodes are located so as to produce an electric field in a direction parallel with said insulator—, and

wherein said thin film transistor is electrically connected to said first electrode.

- 3. (Currently Amended) A light emitting device comprising:
  - a substrate;
- a source wiring over said substrate;
- a gate wiring over said substrate;
- a switching thin film transistor and a current controlling thin film transistor provided in an intersection of said source wiring and said gate wiring;

an insulator over said switching thin film transistor and said current controlling thin film transistor;

an anode a first electrode formed on said insulator;

- not to be in contact with said anode first electrode; and
  - a light emitting layer formed between said anode and said

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cathode first and second electrodes on said insulator,

wherein said anode and said cathode are formed into a comb tooth shape on said insulator and located such that each tooth of said anode are adjacent to each tooth of said cathode. said current controlling thin film transistor is electrically connected to first electrode.

4. (Currently Amended) A light emitting device comprising:

a substrate;

a source wiring over/said substrate;

a gate wiring over said substrate;

at least one thin film transistor provided in an intersection of said source wiring and said gate wiring;

an a first insulator over said thin film transistor;

a power supply lime over said first insulator;

a second insulator comprising resin over said first

insulator and said power supply line;

an anode a first electrode formed on said second insulator;

a cathode second electrode formed on said second insulator

so as not to be in contact with said anode first electrode; and

a light emitting layer formed between said anode and said

cathode first and second electrodes on said second insulator,

wherein said anode and said cathode are formed into a spiral shape on said insulator and located such that each tooth of said anode are engaged with these of said cathode said thin film transistor is electrically connected to said first electrode.

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5. (Currently Amended) A light emitting device comprising:

an insulator;

an anode formed on said insulator;

a cathode formed on said insulator so as not to be in contact with said anode; and

a light emitting layer formed between said anode and said cathode on said insulator,

wherein said light emitting layer is made from comprises a first layer having an electron transport property and a hole transport property and a second layer containing a luminescent material, which is formed on said layer having said electron transport property and said hole transport property. and

wherein said first layer is formed on said anode, said cathode, and said insulator, and said second layer is formed on said first layer.

6. (Currently Amended) A light emitting device comprising:

an insulator;

an anode formed on said insulator;

a cathode formed on said insulator so as not to be in contact with said anode; and

a light emitting layer formed between said anode and said cathode on said insulator,

wherein said light emitting layer is made from comprises a first layer having an electron transport property and a hole transport property and a second layer containing a luminescent material, which is formed on said layer having said electron transport property and said hole transport property.

wherein said first layer is formed on said anode, said cathode, and said insulator, and said second layer is formed on said first layer, and

wherein said anode and said cathode are located so as to produce an electric field in a direction parallel with said insulator.

7. (Currently Amended) A light emitting device comprising: an insulator;

an anode formed on said insulator;

a cathode formed on said insulator so as not to be in contact with said anode; and

a light emitting layer formed between said anode and said cathode on said insulator,

wherein said light emitting layer is made from comprises a

first layer having an electron transport property and a hole transport property and a second layer containing a luminescent material, which is formed on said layer having said electron transport property and said hole transport property,

wherein said first layer is formed on said anode, said cathode, and said insulator, and said second layer is formed on said first layer, and

wherein said anode and said cathode are formed into a comb tooth shape on said insulator and located such that each tooth of said anode are adjacent to each tooth of said cathode.

8. (Currently Amended) A light emitting device comprising: an insulator;

an anode formed on said insulator;

a cathode formed on said insulator so as not to be in contact with said anode; and

a light emitting layer formed between said anode and said cathode on said insulator,

wherein said light emitting layer is made from comprises a first layer having an electron transport property and a hole transport property and a second layer containing a luminescent material, which is formed on said layer having said electron transport property and said hole transport property,

wherein said first layer is formed on said anode, said

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cathode, and said insulator, and said second layer is formed on said first layer, and

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wherein said anode and said dathode are formed into a spiral shape on said insulator and located such that each tooth of said anode are engaged with those of said cathode.

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- 9. (Currently Amended) A light emitting device according to any one of claims 1 to 4, wherein said light emitting layer is comprises a layer having an electron transport property and a hole transport property.
- 10. (Original) A light emitting device according to any one of claims 1 to 8, wherein a reflective film is provided under said light emitting layer.
- 11. (Original) A light emitting device according to any one of claims 1 to 8, wherein said insulator is transparent and a reflective films is provided over said light emitting layer.
- 12. (Currently Amended) A light emitting device according to claim 10 or 11, wherein said reflective film is made of one selected from the group consisting of titanium, aluminum, alloy of titanium and aluminum, silver, or silver alloy.

13. (Currently Amended) A light emitting device according to any one of claims 1 to 8 4, wherein a distance between said anode and said cathode first and second electrodes is 200 nm or shorter.

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14. (Currently Amended) A light emitting device according to any one of claims 1 to 8 4, wherein an angle formed by at least one of a side surface of said anode first electrode or said cathode second electrode or side surfaces of said cathode and said anode and a surface on said insulator is 30° to 90°.

15. (Currently Amended) A light emitting device according to any one of claims 1 to 8 4, wherein one of said anode first and second electrodes comprises a material selected from the group consisting of as gold, nickel, palladium, iridium, and cobalt.

16. (Original) A light emitting device according to any one of claims 1 to 8, wherein said light emitting device is incorporated into an electronic device selected from the group consisting of a display device, a video camera, a head mounted display device, an image back device, a goggle type display device, a portable telephone, a sound reproduction device, and a digital camera.

17. (Previously Added) A light emitting device according to claim 3, wherein said first electrode and said second electrode are formed into a comb tooth shape on said insulator and located such that each tooth of said first electrode are adjacent to each tooth of said second electrode.

- 18. (Previously Added) A light emitting device according to claim 4, wherein said first electrode and said second electrode are formed into a spiral shape on said insulator and located such that each tooth of said first electrode are engaged with those of said second electrode.
- 19. (Previously Added) A light emitting device according to any one of claims 5 to 8, wherein a distance between said anode and said cathode is 200 nm or shorter.
- 20. (Previously Added) A light emitting device according to any one of claims 5 to 8, wherein an angle formed by at least one of a side surface of said anode or said cathode and a surface on said insulator is 30° to 90°.
  - 21. (Previously Added) A light emitting device according to



Corold Q1 any one of claims 5 to 8, wherein said anode comprises a material selected from the group consisting of as gold, nickel, palladium, iridium, and cobalt.

Construction

22. (New) A light emitting device according to claim 11, wherein said reflective film is made of one selected from the group consisting of titanium, aluminum, alloy of titanium and aluminum, silver, or silver alloy.